

0.8 A sensitive gate SCR

Datasheet - production data

Features

- $I_{T(RMS)} = 0.8 A$
- V_{DRM}, V_{RRM} = 600 V
- $I_{GT} = 30 \text{ to } 200 \mu A$

Applications

- Limited gate current topologies
- Ground fault circuit interrupters
- Overvoltage crowbar protection in power supplies
- Protection in electronic ballasts
- Capacitive discharge ignitions
- Ignitors (lighting, oven...)

Description

The X006 SCR can be used as on/off function in applications where topology does not offer high current for gate triggering.

This device is optimized in forward voltage drop and inrush current capabilities for reduced power losses and high reliability in harsh environments.

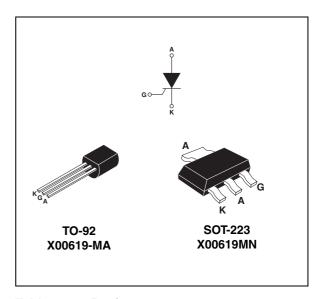


Table 1. Device summary

I _{T(RMS)}	0.8 A
V _{DRM} / V _{RRM}	600 V
I _{GT}	30 to 200 μA

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Table 2. Absolute ratings (limiting values, $T_j = 25$ °C unless otherwise specified)

Symbol	Parameter	Value	Unit		
1	On state rms surrent (190 °Conduction angle)	TO-92	T _L = 83 °C	0.8	Α
I _{T(RMS)}	On-state rms current (180 °Conduction angle) SOT-2		T _c = 107 °C	1 0.0	A
IT.	Average on-state current (180 °Conduction angle)	TO-92	T _L = 83 °C	0.5	Α
IT _(AV)	Average on-state current (160 Conduction angle)	SOT-223	T _c = 107 °C		А
1.	Non repetitive surge peak on-state current	$t_p = 8.3 \text{ ms}$	T _i = 25 °C	10	Α
ITSM		t _p = 10 ms	1 j = 25 C	9	
l ² t	$t_p = 1^2 t$ Value for fusing		T _j = 25 °C	0.4	A ² s
di/dt			T _j = 125 °C	50	A/µs
I _{GM}	Peak gate current $t_p = 20 \ \mu s \qquad T_j = 125$		T _j = 125 °C	1	Α
P _{G(AV)}	Average gate power dissipation	0.1	W		
T _{stg} T _j	Storage junction temperature range Operating junction temperature range				°C

Table 3. Electrical characteristics ($T_j = 25$ °C unless otherwise specified)

Symbol	Test conditions	Value	Unit		
I.			MIN.	30	^
'GT	I_{GT} $V_D = 12 \text{ V}, R_L = 140 \Omega$		MAX.	200	μΑ
V _{GT}			IVIAA.	0.8	V
V _{GD}	$V_D = V_{DRM,} R_L = 3.3 \text{ k}\Omega, R_{GK} = 1 \text{ k}\Omega$ $T_j = 125 \text{ °C}$		MIN.	0.2	V
V _{RG}	I _{RG} = 10 μA		MIN.	5	V
I _H	$I_T = 50 \text{ mA}, R_{GK} = 1 \text{ k}\Omega$		MAX.	5	mA
ΙL	$I_G = 1 \text{ mA}, R_{GK} = 1 \text{ k}\Omega$		MAX.	6	mA
dV/dt	$V_D = 67\% V_{DRM,} R_{GK} = 1 k\Omega$ $T_j = 125 °C$		MIN.	40	V/µs

Table 4. Static electrical characteristics

Symbol	Test conditions			Value	Unit
V _{TM}	$I_{TM} = 1 \text{ A, } t_p = 380 \mu\text{s}$	T _j = 25 °C		1.35	V
V _{TO}	Threshold voltage	T _i = 125 °C		0.85	V
R _d	Dynamic resistance	1j= 125 C	MAX	245	mΩ
I _{DRM} I _{RRM}	$V_{DRM} = V_{RRM}, R_{GK} = 1 \text{ k}\Omega$	T _j = 25 °C		1	μΑ
		T _j = 125 °C		100	μΑ

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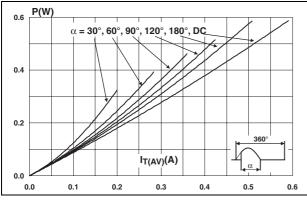
X00619 Characteristics

Table 5. Thermal resistances

Symbol	Parameter Parameter				Value	Unit
R _{th(j-l)}	Junction to leads (DC)		TO-92		70	
R _{th(j-c)}	Junction to case (DC)		SOT-223	May	30	°C/W
D. It is a state of the control of t			TO-92	Max.	150	C/VV
R _{th(j-a)}	Junction to ambient (DC)	$S = 5 \text{ cm}^2$	SOT-223		60	

Figure 1. Maximum average power dissipation versus average on-state current

Figure 2. Average and DC on-state current versus case temperature (SOT-223)



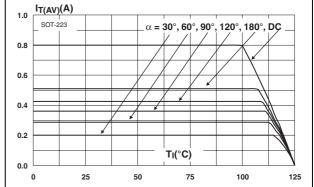
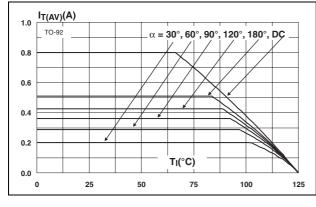
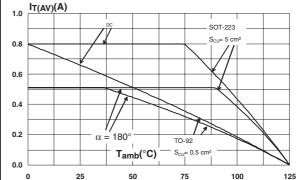


Figure 3. Average and DC on-state current versus lead temperature (TO-92)

Figure 4. Average and DC on-state current versus ambient temperature (free air convection)





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Figure 5. Relative variation of thermal impedance junction to ambient versus pulse duration

1.00 Zth(j-a)/Rth(j-a)

1.00 Sort-223 Scur 5 cm²

1.0E-02 1.0E-01 1.0E+00 1.0E+01 1.0E+02 1.0E+03

Figure 6. Relative variation of gate trigger, holding and latching current versus junction temperature

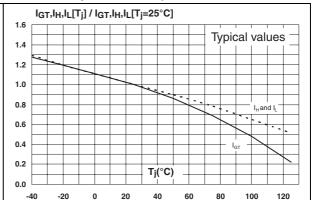


Figure 7. Relative variation of holding current versus gate-cathode resistance (typical values)

7.5 I.Ε-02 1.Ε-01 1.Ε+00 1.Ε+01 1.Ε+02

Figure 8. Relative variation of dV/dt immunity versus gate-cathode resistance (typical values)

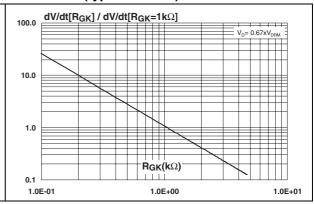
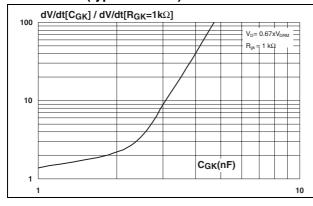
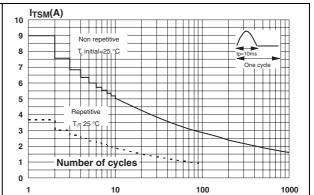


Figure 9. Relative variation of dV/dt immunity Figure 10. Surge peak on-state current versus versus gate-cathode capacitance number of cycles (typical values)





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Figure 11. current for a sinusoidal pulse and corresponding value of I²T

Non repetitive surge peak on state Figure 12. On-state characteristics (maximum values)

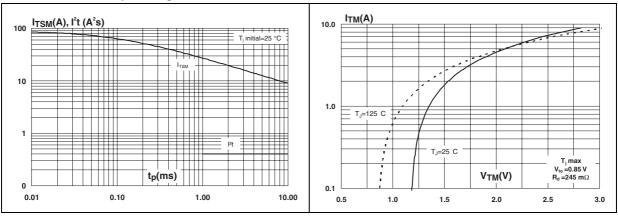
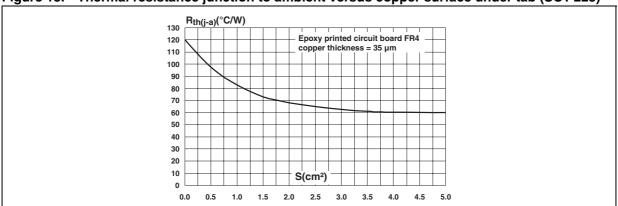
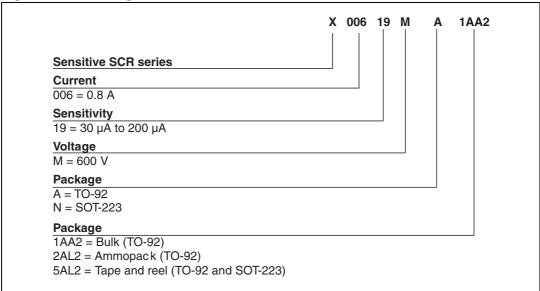


Figure 13. Thermal resistance junction to ambient versus copper surface under tab (SOT-223)



2 Ordering information scheme

Figure 14. Ordering information scheme



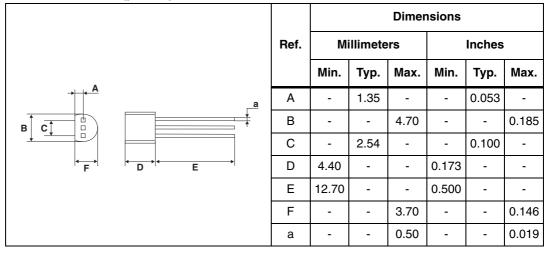
X00619 Package information

3 Package information

- Epoxy meets UL94, V0
- Lead-free packages

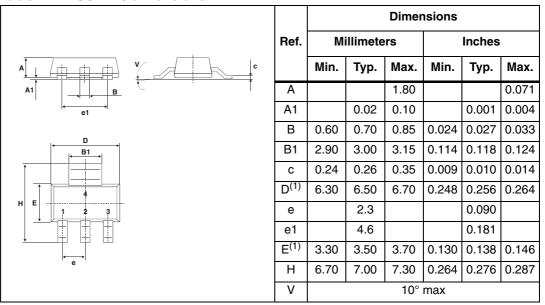
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. TO-92 (plastic) dimensions



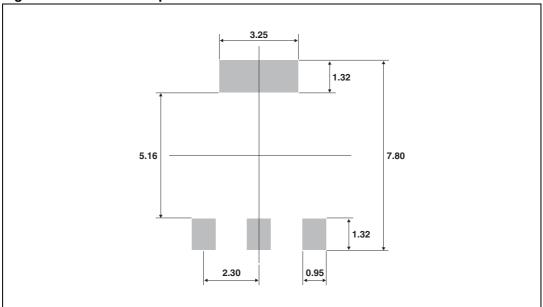
Package information X00619

Table 7. SOT-223 dimensions



^{1.} Do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm (0.006inches)

Figure 15. SOT-223 footprint



4 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
X00619MA1AA2				2500	Bulk
X00619MA2AL2	X0619 MA	TO-92	0.2 g	2000	Ammopack
X00619MA5AL2				2000	Tape and reel
X00619MN5AL2	X0 619 MN	SOT-223	0.12 g	1000	rape and reel

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
26-May-2009	1	First issue
03-May-2012	2	Added SOT-223 package.

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